



STA50X DIGITAL POWER FAMILY

This application note is related to the STA50X series of DDX high efficiency output stages.

1 PIN DESCRIPTION

Table 1. STA500, STA505, STA506, STA508

Pin N°	Pin Name	Description
1	GND_sub	Substrate ground
2	OUT2B	Output Half Bridge 2B
3	OUT2B	Output Half Bridge 2B
4	Vcc 2B	Positive Supply
5	GND2B	Negative Supply (GND)
6	GND2A	Negative Supply (GND)
7	Vcc 2A	Positive Supply
8	OUT2A	Output Half Bridge 2A
9	OUT2A	Output Half Bridge 2A
10	OUT1B	Output Half Bridge 1B
11	OUT1B	Output Half Bridge 1B
12	Vcc 1B	Positive Supply
13	GND1B	Negative Supply (GND)
14	GND1A	Negative Supply (GND)
15	Vcc 1A	Positive Supply
16	OUT1A	Output Half Bridge 1A
17	OUT1A	Output Half Bridge 1A
18	n.c.	Not Connected
19	GND_Clean	Logical Ground
20	GND_Reg	Ground for regulator Vdd
21	Vdd	5V Regulator referred to Ground
22	Vdd	5V Regulator referred to Ground
23	VL(called in previous docs Ibias)	Logic reference voltage

AN1994 APPLICATION NOTE

24	CONFIG	Configuration Pin
25	PWRDN	Stand-by pin
26	TRISTATE	HI-Impedance pin
27	FAULT	Fault pin advisor
28	TH_WAR	Thermal Warning Advisor
29	IN1A	Input Half Bridge 1B
30	IN1B	Input Half Bridge 1B
31	IN2A	Input Half Bridge 1B
32	IN2B	Input Half Bridge 1B
33	Vss	5V Regulator referred to +Vcc
34	Vss	5V Regulator referred to +Vcc
35	VccSign	Signal Positive Supply
36	VccSign	Signal Positive Supply

Table 2. STA501A, STA502A, STA503A

Pin N'	Pin Description		Pin N'	Pin Description
1	GND_sub		19	GND_Clean
2	OUTB		20	GND_Reg
3	OUTB		21	Vdd
4	VccB		22	Vdd
5	GNDB		23	VL
6	GNDB		24	n.c.
7	n.c.		25	PWRDN
8	OUTA		26	TRISTATE
9	OUTA		27	FAULT
10	n.c.		28	TH_WAR
11	n.c.		29	n.c.
12	VccA		30	n.c.
13	GNDA		31	INA
14	GNDA		32	INB
15	n.c.		33	Vss
16	n.c.		34	Vss
17	n.c.		35	VccSign
18	n.c.		36	VccSign

Table 3. STA501, STA502, STA503

Pin N'	Pin Description		Pin N'	Pin Description
1	GND_sub		19	GND_Clean
2	OUTB		20	GND_Reg
3	OUTB		21	Vdd
4	Vcc		22	Vdd
5	GNDB		23	VL
6	GNDA		24	CONFIG
7	Vcc		25	PWRDN
8	OUTA		26	TRISTATE
9	OUTA		27	FAULT
10	n.c.		28	TH_WAR
11	n.c.		29	GND
12	Vcc		30	GND
13	GND		31	INA
14	GND		32	INB
15	Vcc		33	Vss
16	n.c.		34	Vss
17	n.c.		35	VccSign
18	n.c.		36	VccSign

2 CONTROL PINS

Table 4.

Pin Name	IC-Status	Logic Value	Notes
TH WAR	Normal operation	1	Open collector. To have high logic value is necessary a pull-up resistor
	IC temperature = 130°C	0	
FAULT	Normal operation	1	Open collector. To have high logic value is necessary a pull-up resistor
	Fault detected (Short circuit, Thermal...)	0	
TRI-STATE	Normal operation	1	
	All powers in Hi-Z state	0	
PWRDN	Normal operation	1	
	Low absorption	0	
CONFIG	Normal operation	0	
	OUT1A=OUT1B; OUT2A=OUT2B (If IN1A=IN1B; IN2A=IN2B)	1	CONFIG=1 means connect Pin 24 (Config) to pins 21, 22 (Vdd)

2.1 INPUT CONTROL PINS

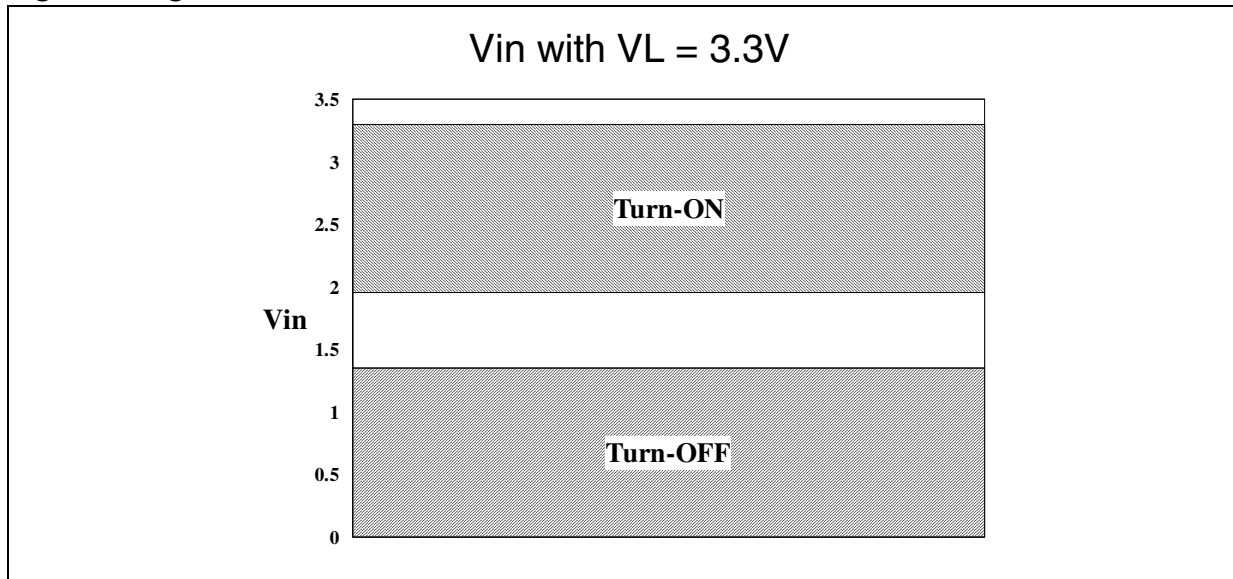
- PWRDN: pin 25
- TRI-STATE: pin 26
- CONFIG: pin 24

Input control pins (PWRDN and TRI-STATE) are connected to the high impedance input of a CMOS Schmitt trigger.

The **PWRDN** pin is also connected through an high value (100 KOhm) pull-down resistor to GND (specified 35/uA @ V_pwrdsn=3.3V)

The **TRISTATE** pin has not pull down.

Figure 1. Figure VL threshold



The Schmitt triggers thresholds are, for both pins in the range of 1.5V at TURN ON (V_H) and 1.3 at TURN OFF (V_L), when $V_L=3.3V$ (are V_L dependent). Then the hysteresis interval is well inside the standard logic interval for inputs specified in the datasheet (0.8 - 1.7V @ $V_L=3.3V$; for different V_L see table under note 1).

The **CONFIG** pin in stereo configuration, should be connected to digital GND, but as general remark, should be noted that all the GND's on the recommended layout, are connected together by a wide GND plane.

2.2 OUTPUT CONTROL PINS

- FAULT: pin 27
- TH_WAR: pin 28

Outputs control pins (FAULT and TH_WAR) are open drains pin; they need an external pull-up resistor.

2.2.1 FAULT

The FAULT is activated when one of the following conditions occur:

UNDERVOLTAGE:	power supply	$V_{CC} < 7V$ (typ.)
OVERTEMPERATURE:	junction temperature	$T_j > 150^\circ C$ (typ)
LOGIC UNDERVOLTAGE:	Logic supply	$V_L < 0.9V$
OVERCURRENT:	Output current	
	STA500	$I_{out} > I_{sc} = 3.5A(\text{min}) - 5 A$ (typ)
	STA501	$I_{out} > I_{sc} = 3.5A(\text{min}) - 6 A$ (typ)
	STA502	$I_{out} > I_{sc} = 4A(\text{min}) - 6 A$ (typ)
	STA503	$I_{out} > I_{sc} = 4.5A(\text{min}) - 6 A$ (typ)
	STA505	$I_{out} > I_{sc} = 3.5A(\text{min}) - 6 A$ (typ)
	STA506	$I_{out} > I_{sc} = 4A(\text{min}) - 6 A$ (typ)
	STA508	$I_{out} > I_{sc} = 4.5A(\text{min}) - 6 A$ (typ)

OVERVOLTAGE: in STA50x the circuitry is present but the threshold is intentionally set at a value higher than the absolute maximum rating (40V), so STA50x is not over-voltage protected.

The absolute maximum rating that must not be exceeded (even during commutation spikes) is 40V: above this value the device could be damaged.

UNDERVOLTAGE: the typical is activated threshold is 7V.

OVERTEMPERATURE: the threshold junction temperature is 150°C ($\pm 10^\circ\text{C}$), there is no hysteresis (fast oscillations are prevented by the turn on delay). The threshold for FAULT and TH_WAR are in tracking.

OVERCURRENT: the minimum overcurrent value for all IC is shown in the previous table. For normal operation the peak value through the load must be less than the overcurrent limit.

An internal delay of about 200nsec prevents the current limiter intervention for current spikes occurring during normal operation. The device is not protected against the direct short on the pin before the inductor. It is important that the selected inductor doesn't saturate for the rated specified current.

2.2.2 THERMAL WARNING

The Thermal Warning pin is activated low (open-drain MOSFET) when the IC junction temperature exceeds 130°C.

This allows acting on the input signal in order to decrease the dissipated power. This avoids the fault intervention (150°C).

3 POWER SUPPLIES PINS

3.1 GND_SUB

This pin is connected to the substrate of the IC and to the slug

3.2 GND_Clean

This pin is the reference GND for all input logic signals, so it must be as clean as possible.

Is recommended not connect directly this GND with other GNDs (i.e. speaker GND) that are interested by voltage spikes.

3.3 GND_Reg

This pin is necessary to filter an internal reference voltage (Vdd); it should be connected via a capacitor to Vdd.

3.4 GND1A - GND1B - GND2A - GND2B

These pins are power grounds interested by high currents generating spikes.

In order to improve EMI and the other problems as false commutations or disturbances is strongly recommended to connect them to a GND plane star routed to the input electrolytic capacitors.

When the slug down package is used (STA500), the GND plane connected to these pins and to the slug must be carefully dimensioned in order to dissipate the generating heating.

3.5 Vcc1A - Vcc1B - Vcc2A - Vcc2B

These power pins must be externally filtered via capacitors placed as close as possible.

This to avoid that the high voltage spikes externally generated could affect the operation and the reliability.

3.6 V_L ($2.7V < V_L < 5.5V$)

V_L pin must be connected to the logic supply of the modulator in order to guarantee the correct the logic thresholds.

To V_L are connected:

- Resistive dividers (the other side connected to GND_Clean) to fix the threshold of logic inputs (IN1A, IN1B, IN2A, IN2B) see datasheet High/Low level input voltage = $(V_L/2) \pm 300mV$;
- Supply of input Schmitt triggers for control inputs PWRDN and TRISTATE as in table in Note1.
- The logic circuits inside the STA50x are powered from Vdd (internally generated from the power supply Vcc and externally filtered by C58)

3.7 Vdd

These pins (pin 21 and 22) are internally connected to a voltage reference 5V referred to GND. These pins require a bypass capacitor.

3.8 VccSign

These pins (pin 35 and 36) are signal positive supply.

3.9 Vss

These pins (pin 33 and 34) are internally connected to a voltage reference 5V referred to Vcc. These pins require a bypass capacitor.

4 INPUT AND OUTPUT PINS

4.1 IN1A, IN1B, IN2A, IN2B

There are four input pins, one for each half bridge (IN1A - 29, IN1B - 30, IN2A - 31, IN2B - 32). They are high impedance logic inputs, without any pull-up or pull-down resistors. If unused they MUST be connected either to GND-Clean (pin 19) or to the logic supply V_L (pin 23).

Each input pin is connected to the input of a comparator (gate of a PMOS differential pair), with the second input (reference) tied to the central tap of a divider ($10K\Omega + 10K\Omega$) connected between the pin V_L and GND-Clean. So the logic threshold equals to half logic supply voltage ($V_L/2$) is provided. Each comparator provides also a small hysteresis.

The input pins are ESD protected via an internal diodes network.

4.2 OUT1A, OUT1B, OUT2A, OUT2B

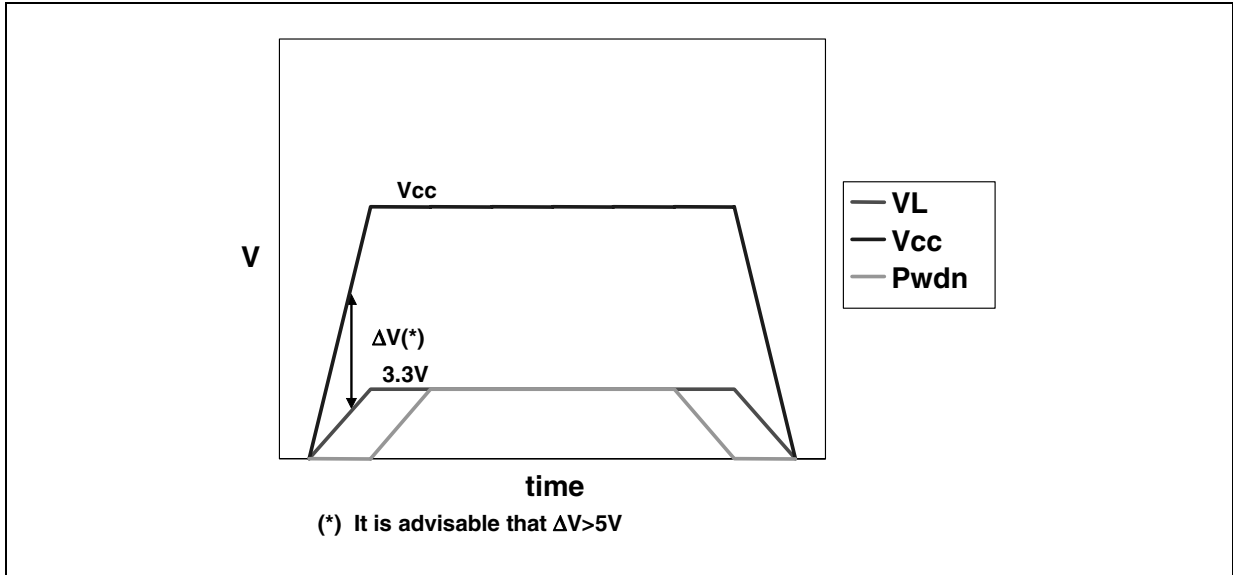
There are 8 pins (4 pins for STA501A, STA502A and STA503A) used for output signals.

These pins carry the high voltage PWM signal that once filtered (via the low pass Butterworth) can be applied to the speakers.

A snubber RC network must be connected as close as possible to the pins in order to improve EMI performances that could be affected by the ringing generated in the PWM waveform.

5 V_L AND V_{CC} POWER ON SEQUENCE

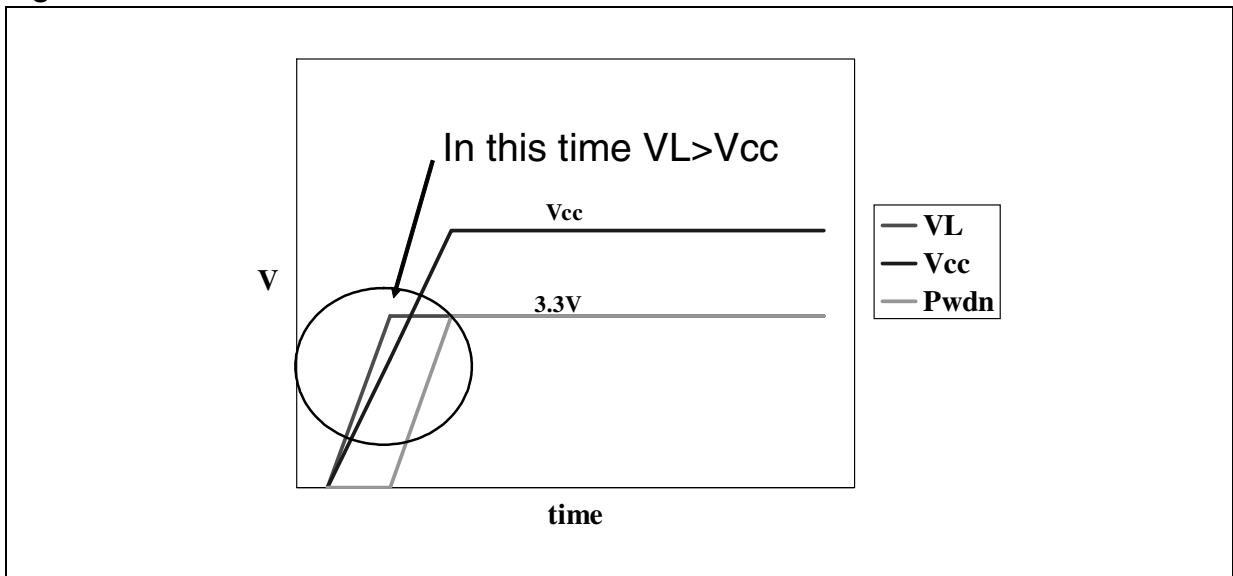
Figure 2. TURN ON SEQUENCE



If the sequence turns on V_L before V_{CC} (how shown in next figure) an uncontrolled current could flow through the ESD protection diode from V_L (logic supply) to V_{CC} (high power supply). That can cause:

- a) Damage the ESD diode;
- b) Switch on some parasitic latch that sustains itself also when both supplies are growing to the steady value;

Figure 3. WRONG TURN ON SEQUENCE



6 POWER DOWN SIGNAL DURING POWER ON

- 1) To have the application working correctly PWRDN must be derived from a logic powered from V_L , than Power Down cannot go before V_L .
- 2) If some fault occurs nothing happens, in any case PWRDN has to go high AFTER V_{cc} to avoid forward bias of the usual ESD diode and also some other parasitic.

7 PROTECTION

When an overcurrent is detected, a Flip-Flop, representative of the FAULT state, is set to TRUE, the output of this Flip-Flop shuts down immediately all the output power stages, putting all the output in HIGH IMPEDENCE status.

At the same time an open drain transistor, connected to the output pin FAULT (pin 27) is switched ON.

The FAULT Flip-Flop can be RESET to FALSE state (normal operation) putting the input pin TRISTATE (pin 26) to logic value ZERO.

Two ways of operation, depending on the application, are then possible.

7.1 SHUT DOWN MODE

FAULT (pin 27) and TRISTATE (pin 26) pins are independent (FAULT is pulled up). In case of fault conditions, the device is shut down and the FAULT status is flagged on pin 27 that becomes logic LOW.

The normal operation can be restarted cycling the pin TRISTATE LOW and then HIGH by an appropriate external signal.

7.2 AUTOMATIC RETRYING MODE (recommended)

FAULT and TRISTATE pins are shorted together and connected to a timing capacitor (C58, refer to the datasheet) and to an external signal through a resistor, as in the current application.

During the FAULT condition a RESET is activated, forcing low the TRISTATE pin.

The normal operation is automatically restarted pulling the TRISTATE pin LOW (under the reset threshold) and then leaving it to go HIGH (over the normal operation threshold) in sequence with a time constant set by the external RC.

If the FAULT condition is still present (e.g. an overload not removed) the cycle off-on is repeated: on the delay capacitor is visible a saw tooth waveform. Increasing the capacitor value, the retrying frequency will be lowered increasing the reliability.

7.3 NOTES:

- Before to the FAULT Flip-Flop the overcurrent signal is in OR with other fault conditions (thermal high, Over Voltage, Under Voltage)
- The FAULT Flip-Flop is set dominant, that is in case of a permanent FAULT, the restart cannot happen until the fault condition is removed.
- In both the ways of operation, the protection of the device is dominant and immediate, only the restart is different.

7.4 RECOMMENDATIONS about short circuit protection.

The devices are short circuit protected, but the operation of the protection circuit could be affected by external causes as:

- PCB Layout;
- External delay;
- Butterworth filter components;
- Vcc decoupling.

Even if the overcurrent protection is correctly working, its effectiveness is related not only to the IC, but also to several aspects of the application and PCB layout:

- A delay after a short and before a retrying is mandatory. A delay in the range of milliseconds if logic or given by the application diagram if set by an RC time constant is the absolute for a correct behavior. Delays of one or two of magnitude bigger (obtained increasing C14) are recommended to improve the robustness especially in demanding application (e.g. C14 = 4.7 μ F for single BTL application). In typical double BTL application the components values are: C=100nF and R=10K Ω (R*C = 1sec).
- The correct bypassing of the supply rails is mandatory to keep the voltage spikes below the Absolute Maximum Rating
- The inductors cores must not saturate until the maximum threshold value of the short circuit current limit (Ish), to assure an incremental self-inductance big enough to limit the current increase during the blanking period. Note that in single BTL operation, the current through the inductors is doubled and can reach high values.

8 OUTPUT MINIMUM PULSE WIDTH

To avoid multiple commutations caused by the current switched by the output stage, is introduced an internal fixed blanking delay T.

After each transition, the device goes in a blanking state and does not accept any new input state (in other words the input is frozen) for the time T.

Because of this, any input pulse (eventually shorter than T) is lengthened to a time T. The delay time T could vary from a minimum 70nsec to a maximum of 150nsec.

The maximum switching frequency is limited also by the modulation system used and the duty cycle that must be reached.

With fixed frequency PWM a maximum duty-cycle = 94%, imposing a minimum pulse width of 150nsec, gives a maximum switching frequency around 400KHz.

Note that the efficiency is decreasing when the switching frequency increases due to the switching/gate charging losses.

9 OUTPUT POWER

Definition of symbols:

R_{ds_on} = Power Pchannel or Nchannel mosfet R_{ds_on} (each transistor)

I_{sc} = Short circuit current limit (each transistor)

T_{pw_min} = Output minimum pulsewidth

F_{sw} = Switching frequency

Mi_max = Maximum modulation index

The Mi_max is dependent from the modulator kind and from the switching frequency.

$T_{pw_min(max)} = 150\text{nsec}$
 For DDX modulator: $F_{sw}=385\text{KHz}$;

$$M_{i_max} = 1 - F_{sw} \cdot T_{pw_min(max)} = 1 - 0.385\text{MHz} \cdot 0.150\mu\text{sec} = 0.94$$

The calculations for output power are done in the straight forward case in which the device is reproducing an undistorted sinusoid (crest factor equal to $\sqrt{2}$).

In the case that the device is reproducing a 10% sinusoid distorted by clipping, the multiplication factor is:

$$P_{out}(\text{SIN@THD}=10\%) = 1.28 \cdot P_{out}(\text{SIN_undistorted})$$

In the limit case in which the device is reproducing a square wave (crest factor equal 1), the multiplication factor is:

$$P_{out}(\text{SQUARE}) = 2 \cdot P_{out}(\text{SIN_undistorted})$$

The **undistorted output power** is given by (sinusoidal output for each channel):

$$P_{out} = \frac{(M_{i_max} \cdot V_{cc})^2}{2 \cdot (R_{load} + 2 \cdot R_{ds-on})^2} \cdot R_{load}$$

The peak current flowing through the device (each channel) is

$$I_{peak} = \frac{(M_{i_max} \cdot V_{cc})}{2 \cdot (R_{load} + 2 \cdot R_{ds-on})}$$

Taking account of the worst case spreads, the conditions to start is:

$$I_{peak_max} < I_{sc_min}$$

To be sure not to have the switch off of the device due to the intervention of the short circuit protection in some limit conditions.

Solving the formula to find V_{cc_max} ,

$$V_{cc_max} < I_{sc_min} \cdot \frac{R_{load-(min)} + 2 \cdot R_{ds-on(min)}}{M_{i_max}}$$

$$V_{cc_max} < 40 \text{ for STA50x}$$

9.1 WARNING:

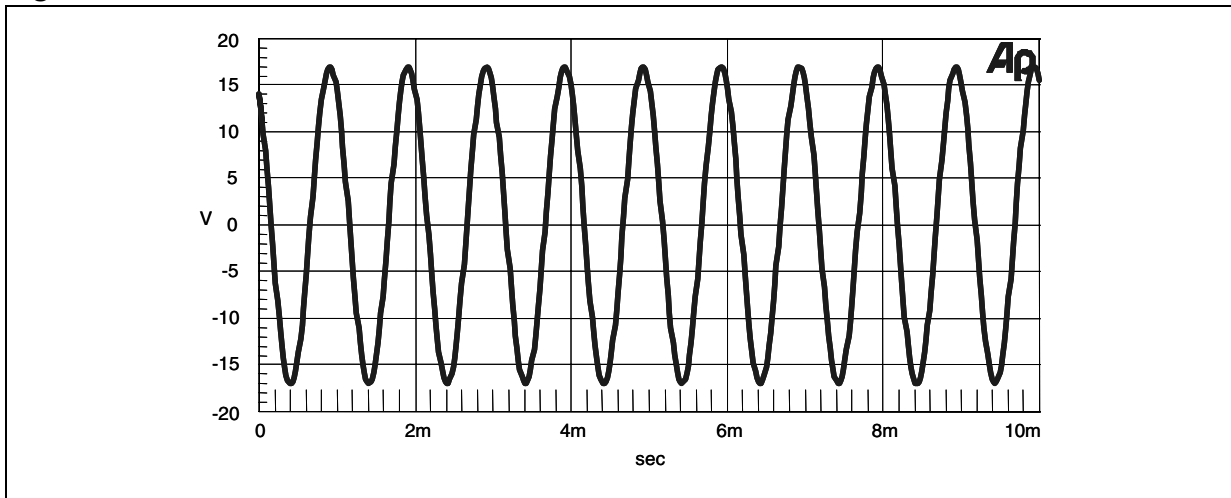
When THD=10%, if exists on the modulator the gain compressor, the I_{peak} is constant (same as THD=1%) and increases the I_{rms} .

In fact the wave without gain compressor saturates how showed in next figure.

Numerical example:

$V_{cc} = 20\text{V}$; $R_{load} = 8\Omega$;

Figure 4. Audio Precision



Output power: 18.4W; Output = 0dB; THD = 1%

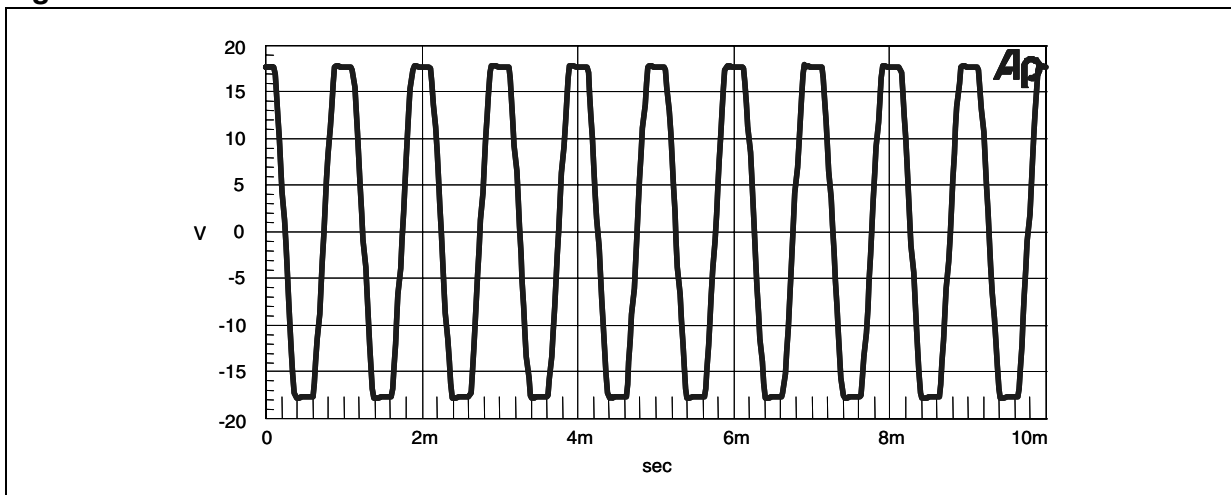
$$P_{out} = \frac{(V_{cc} \cdot M_i)^2}{2 \cdot (R_{load} + 2 \cdot R_{ds-on})^2} \cdot R_{load}$$

From the previous formula, results:

$$V_{cc} \cdot M_i = 18V$$

$$I_{peak} = \frac{P_{out}}{R_{load}} = 2.25A$$

Figure 5. Audio Precision



Output power: 18.4W; Output = 0dB; THD = 1%

$$P_{out} = 1.28 \cdot P_{out} (@THD=1\%)$$

I_{peak} remains constant at 2.25A because the waveform is not a sine but it is a saturate sine (with the peak equal to 0dB).

10 DIFFERENT APPLICATIONS

10.1 General properties

10.1.1 Power supply bypass capacitor.

The power supply bypass capacitors (namely C30, C31, C32, C33) are used to filter the fast current transients (10 to 20 nsec) due to the switching; avoiding spikes caused by the stray parasitic inductance of the PCB tracks.

The correct values are 1uF and 100nF for each channel (e.g. C30=C32=1uF and C31=C33=100nF). To be effective those capacitors MUST:

- a) Have low parasitic series impedance (inductance) at high frequency (e.g. X7R dielectric);
- b) Be of surface mounting (leadless chip) kind;
- c) Be connected as close as possible to the IC: the direct connection to the related Vcc and GND pins of the IC is recommended.

Please, note that an inductance due to a PCB track of only ~15mm submitted to a current variation of ~3A in 15nsec, generates spikes in the range of 3V.

10.1.2 PCB layout.

The PCB layout must follow the style and guidelines used for High Frequency (e.g. use of the ground layer and wide supply tracks to minimize the stray inductances as much as possible). Vias are connected to Vcc trace on bottom of pc board. Vcc trace is continuous between vias. Connection must be short and direct.

Vias are connected to GND plane on bottom of PC Board. GND plane is continuous between vias. Connections must be short and direct.

If GND trace is long inductive and not continuous between vias, this is dangerous and it can damage the STA50x.

10.1.3 Electrolytic capacitor.

The electrolytic capacitor C55 (1000uF) has the aim to filter the switching frequency and its harmonic components, so shall be connected as close as practical to the IC and shall have relatively good high frequency characteristics. In any case the interpositions of long wires/tracks or filtering beads/chokes between C55 and IC must be absolutely avoided.

10.1.4 Logic supply bypass capacitor.

The capacitors C53, C58 (between pin 20 and pins 21, 22) and C60 bypassing the self regulated low voltage supplies Vdd (pins 20, 21) and Vss (pins 33, 34) to the relative power supply Vcc-sign (pins 35, 36) and GND_reg (pin 20) are also important: so must be as close as possible of the IC and have good HF characteristics.

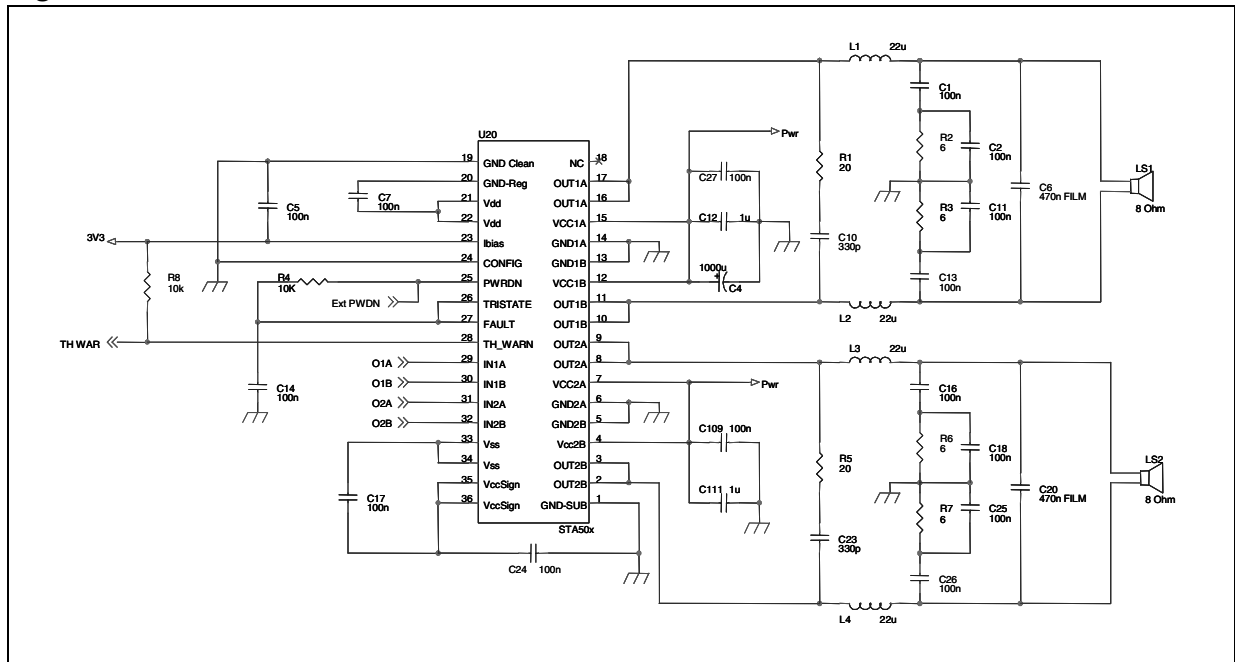
10.1.5 Output Inductors.

These inductors (L3, L4, L5, L6) **must be** separated for best performance. Placing inductors very close will greatly increase crosstalk and distortion caused by magnetic coupling.

10.1.6 Snubber circuit.

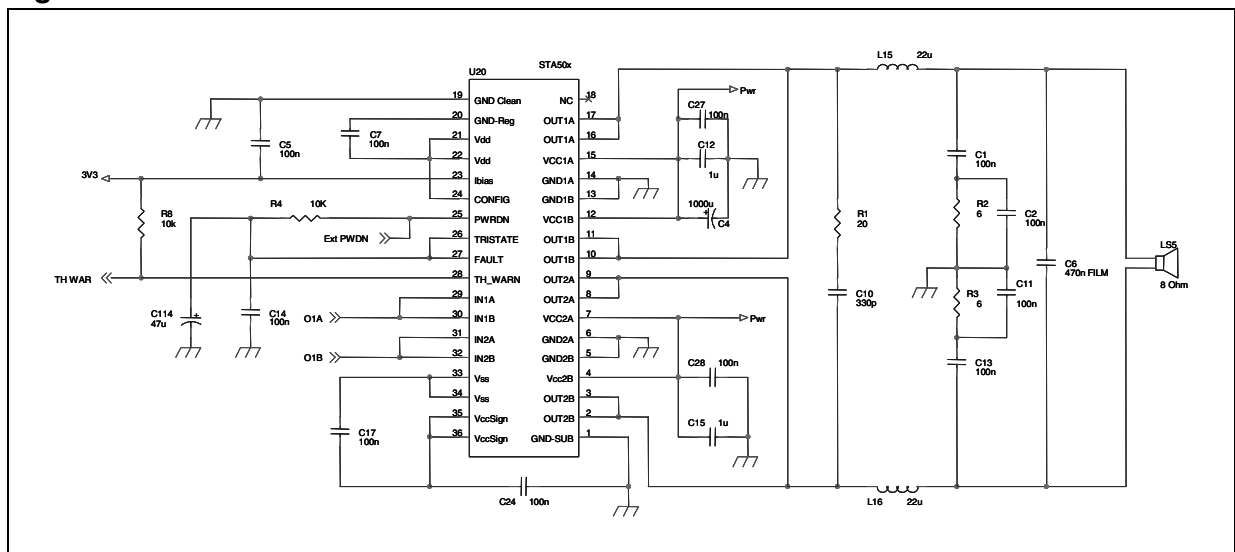
Snubber resistor and capacitor are required and must be SMDs. Also snubber networks have to be mounted near the IC.

Figure 6. DOUBLE BTL



10.2 SINGLE PARALLELED BTL

Figure 7.



10.2.1 Note on Single BTL application.

The CONFIG pin (24) must set HIGH, connecting it to Vdd pin (22) and the output pins must be connected as follows: OUT1A (pins 16, 17) together OUT1B (pins 10, 11) and OUT2A (pins 8, 9) to OUT2B (pins 2, 3).

The pin IN1A (29) must be connected to IN1B (30) and IN2A (31) to IN2B (32). The paralleled input pins must be connected to the outputs of a suitable PWM modulator.

According to the datasheet, using the single BTL configuration, for the couple of the paralleled

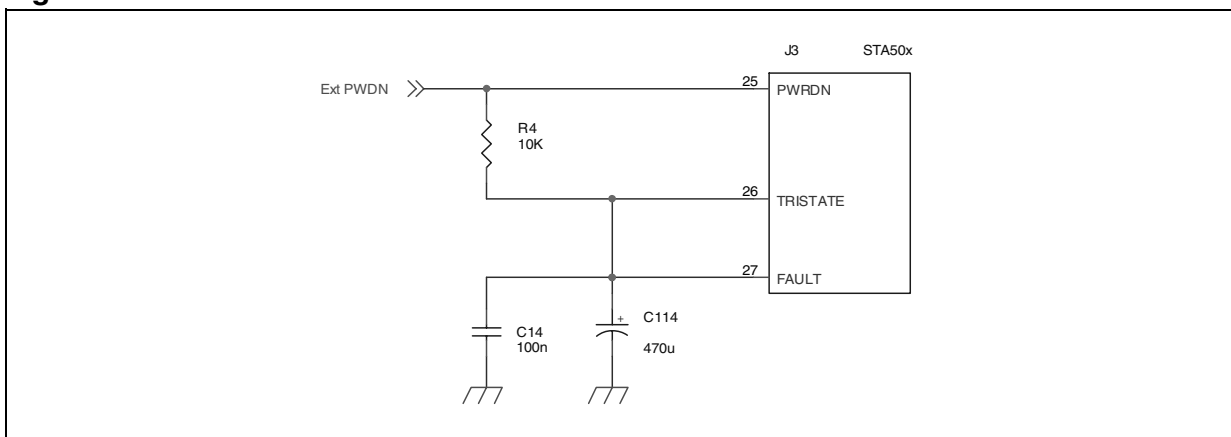
channels:

- The Rds_on is halved.
- The current capability is doubled, so is doubled the short circuit limiting threshold.
- The leakage current is doubled.
- All other parameters remain unchanged.

Switching simultaneously high currents, this configuration is more critical than the double bridge for the PCB layout and supply bypassing, especially when it is working near the maximum allowed voltages and currents and during eventual overloads, and short circuits.

In order to improve reliability in short circuit conditions, the circuitry applied to the PWRDN, FAULT, TRISTATE pins must be modified as follows.

Figure 8.

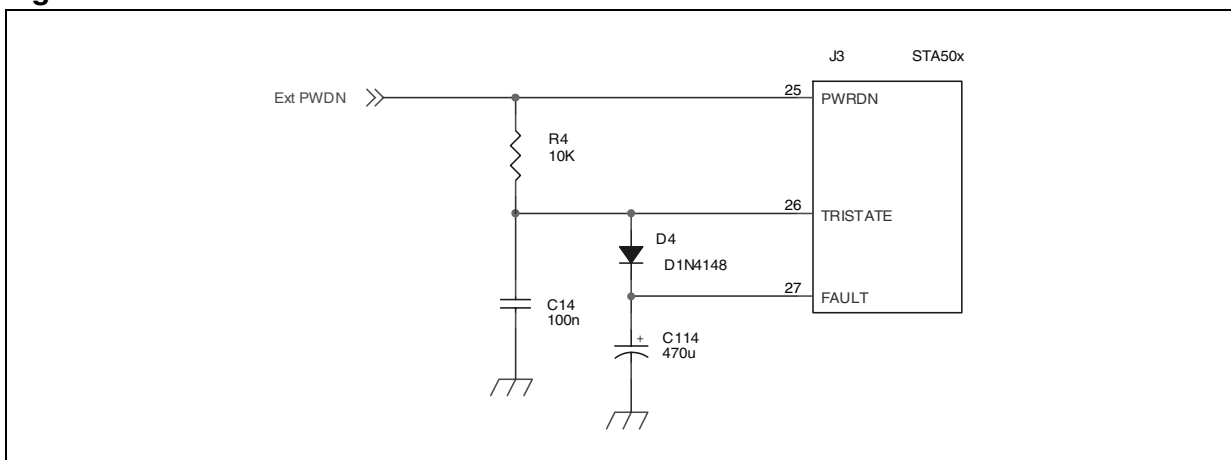


Usually, the time constant necessary to automatically restart the device when a fault condition is present is dictated by R4, C114 time constant (~4sec).

When the start is set via an Ext PWDN signal is advisable to reduce this time constant implementing the following circuitry. This avoids waiting for a long period of time to hear music if a fault condition is not present.

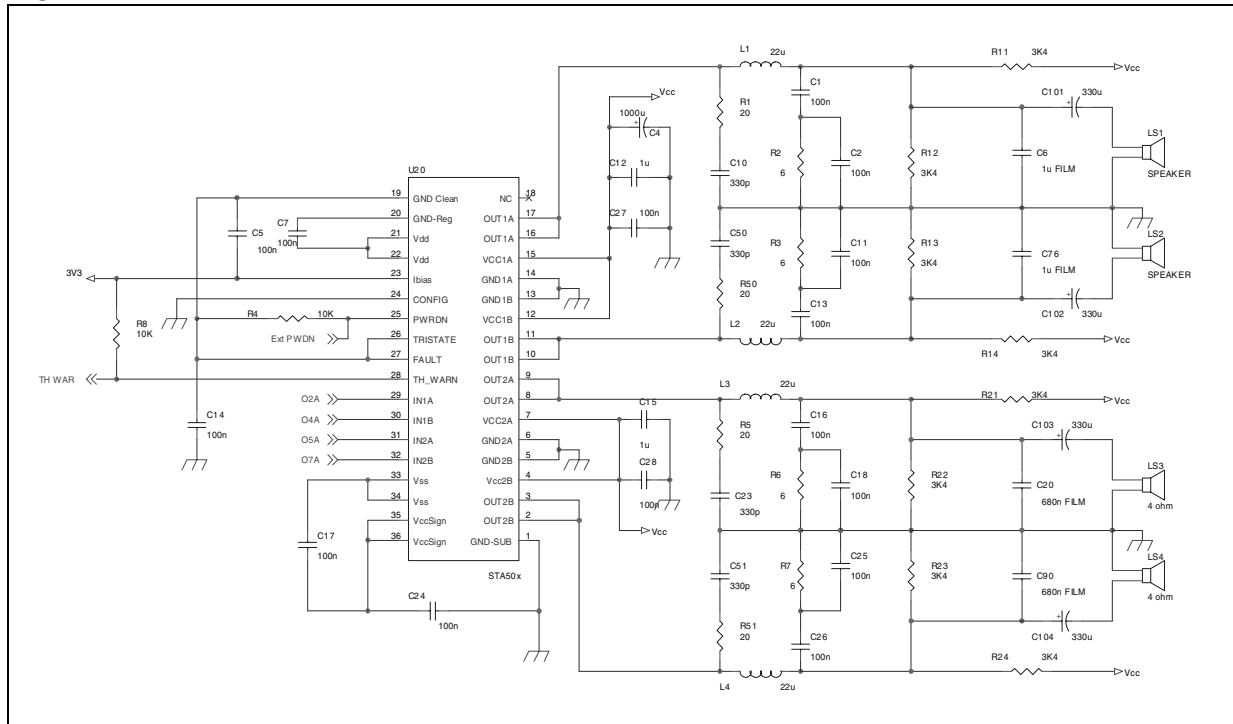
This method provides two time constants a short one for Ext PWDN and longer one for FAULT. However one point that must be noted is that the first power on the time constant will be longer around 3.5sec as the capacitor C114 (470µF) has to get charged initially.

Figure 9.



10.3 SINGLE ENDED

Figure 10.



In single ended, with low signal (at limit 0), the load is connected to the supply for about half of time, so Power Supply Rejection is low. For comparison, in BTL structure at low signal, the load is connected to the supply for a short time (at limit 0), so the Power Supply Rejection is good.

For low frequencies, due the cutoff frequency of the DC decoupling capacitor on the load resistor, the S/N ratio is decreasing because:

- At first order the output signal is decreasing because of the cutoff;
- At second order, the chemical capacitor is significantly charging and discharging following the signal (not just holding the $V_{supply}/2$ potential as with an high frequency signal), so its own no linearity can increase the THD.

Usually this should be not a problem, because those frequencies are of no interest: please consider THD only in the flat zone or increase the capacitor value accordingly to the lowest frequency of interest.

- At signal frequencies approaching the cutoff frequency, with big output signal, the peak current, due to the charge-discharge of the decoupling capacitor, increases significantly. This can be carefully considered to avoid the switch off due to the overcurrent protection.
- For all those reasons it is recommended not to input signals at a frequency lower than the cutoff frequency $1/2\pi * C_{load} * R_{load}$

Single Ended is worst in THD than BTL also just because single ended is asymmetric where BTL is SYMMETRIC, so in single ended are present both EVEN and ODD harmonics, in BTL only ODD harmonics.

It is important to verify the correct phasing of PWM input of every IC.

In fact, in other case there are some crosstalk problems (increase the THD...). Optimal mapping of PWM output channels to a single power device should be 90° apart). With DDX@ modulation it is recommended to connect channels 2, 4, 5, 7 to one power device and 1, 6 to the second device.

10.3.1 Single ended Advantages

- Reduced system cost
- Simpler, smaller design, lower parts count

10.3.2 Single ended Disadvantages

- Less available power per channel
- Lower SNR
- Higher crosstalk
- Less “pop” immunity

10.3.3 Output power for Single Ended Application.

In this type of application the output signal varies from 0 and Vcc. The electrolytic capacitor (C2) makes to remove the continuous component output power.

On the output load the signal varies from -Vcc/2 and +Vcc/2, with correction factor depending from the Modulation Index (Mi_max).

The R_{ds_on} is halved because only one power MOS is used. (→R_{ds_on} = 200mΩ).

The Mi_max is:

$$Mi_{max} = 1 - 2 * Fsw * Tpw_{min(max)} = 1 - 2 * 0.385MHz * 0.150\mu sec = \mathbf{0.88}$$

$$P_{out}(@THD = 10\%) = \frac{\left(\frac{V_{cc} \cdot Mi_{max}}{2}\right)^2}{2 \cdot (R_{load} + R_{ds-on})^2} \cdot R_{load} = \frac{(V_{cc} \cdot Mi_{max})^2}{8 \cdot (R_{load} + R_{ds-on})^2} \cdot R_{load}$$

The output power in single ended is less than one quarter of output power in double BTL.

10.3.4 Filter components

- L1 and C1 constitutes the main filter, the values have to be chosen to constitute a Butterworth filter with the load impedance (loudspeaker), and the cutoff frequency has to be chosen between the upper limit of the audio band has to be reproduced and the carrier frequency as starting value, good for Rload = 4ohm, you can choice L1 = 22μH and C1=1μF (film capacitor) for a cut-off frequency fc≈34KHz.
- Rd and Cd is a dumping network, to be used with highly inductive loads, at first try not use.
- R1 and R2 are two equal resistors to take the output at half supply when the STA50x is in tristate.

The aim is to charge slowly the decoupling capacitor at the turn-on of the power supply avoiding pops. Of course, the STA50x must go in play only after that the capacitor is fully charged and the modulator must at this instant supply the inputs with a 50% duty cycle at first, corresponding to zero audio level.

- C2 is the usual huge chemical output DC decoupling capacitor. Its value is related to the load impedance and the lower limit of the audio bandwidth.

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Table 5.

Loudspeaker	8Ω	6Ω	4Ω
L1	47μH	33μH	22μH
C1	390nF	470nF	680nF
R1 – R2	6.2KΩ	4.7KΩ	3.4KΩ
C2	180μF	220μF	330μF

– C2 is determined using the formula:

$$C2 = \frac{1}{2 \cdot \pi \cdot f_{3dB} \cdot Z_{spkr}} \quad \text{with } f_{3dB} = 120\text{Hz}$$

– C2 requires time to be charged to operating voltage before applying the output section to the speaker. If the speaker is connected before C2 is charged, the difference between the uncharged capacitor voltage and the operating voltage will cause an audible “POP” at the speakers. For no POP on start-up, the STA50x power device is muted for 2 or more RC time constant, where R = R1 and C = C2. The driver or system MCU performs this delay.

For improved crosstalk performance, C2 can be ‘split’ in two capacitors, one connecting to +Vcc and one to GND as seen in next figure. C2 and C3 are 82μF for 8ohm speakers, 100μF for 6ohm speakers and 180μF for 4Ω speakers.

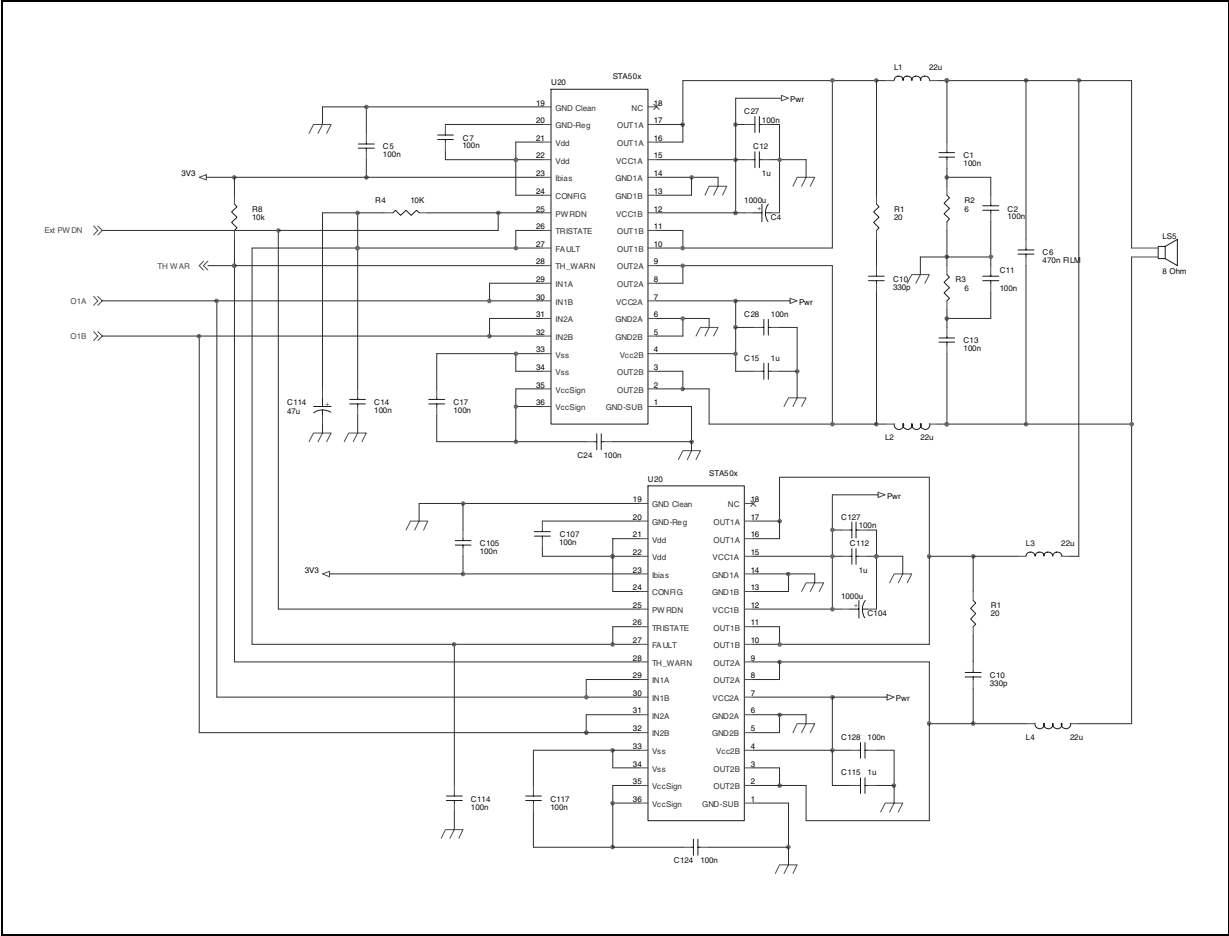
Table 6.

Loudspeaker	8Ω	6Ω	4Ω
L1	47μH	33μH	22μH
C1	390nF	470nF	680nF
R1 - R2	6.2KΩ	4.7KΩ	3.4KΩ
C2 – C3	82μF	100μF	180μF

For no “POP” on start-up the STA50x power device is muted for 4 or more RC time constant where R = R1 and C = C2.

10.4 PARALLELED

Figure 11.



To drive loads having very low impedance obtaining higher output power it is possible to furtherly connect together on the same load two STA50x IC's (each one already configured as single-paralleled bridge) doubling the current capability.

The correct connection is putting together the inductor (L1 with L3 and L2 with L4) terminals on the load side. This to avoid uncontrolled shootrough current spikes, due to time mismatch between the two IC's, which could be possible if the outputs are directly paralleled on the same inductor.

The L and C values of the output filter have to be calculated tacking in account the load impedance: to be noted that the inductance is now provided by two self-inductors in parallel (L1/L3 and L2/L4), so each one must have double value.

The inputs must be driven in parallel.

11 COMPONENT SELECTION GUIDE

11.1 C12, C15: 1 μ F 50V \pm 20% Tantalum Electrolytic

These are Power supply bypass capacitors and must be tantalum type. The normal Aluminum Electrolytic Capacitors have high ESR compared to tantalum electrolytic. The package density is higher for tantalum compared to aluminum electrolytic also. The SMD package is important because this will give less lead inductance and in turn help bypass high frequency on power supply. The important specification to look for is dissipation factor, (tan d) which is typically around 0.04 max. The surface mount EIA size B so that it can be placed close to the power chip. It is also possible to use MLC X7R types; never use Y5V or Z5U type at these locations.

11.2 C7, C17, C24: 100nF 50V X7R \pm 10%

These capacitors are used for bypassing the internal regulator voltage references. These must be, multi layer chip (MLC) type with DC voltage rating of 50V. The important specification to look for is the dielectric type. It must be X7R dielectric and the tolerance must be \pm 10%.

The reason for selecting X7R type is the capacitance stability over temperature the more popular Y5V and Z5U types are not recommended.

The temperature coefficient is important because STA50x power chip uses the heatsink (STA500 uses the PCB copper as heatsink) so nearby capacitors to power chip can drift in capacitance. This capacitance drift can destabilize internal regulator reference voltages. See the typical curves for temperature coefficient curve from MFR.

It is recommended to use surface mount SM0805. This will let you to place them very close to IC in the PCB layout avoiding problems due to spikes generated by switching transients.

11.3 C10, C23: 330pF, 100V, X7R \pm 10%

These form a snubber circuit along with resistors R1 for C10 and R5 for C23 respectively. These also MUST be MLC X7R types with 100VDC rating. The 100VDC rating is specified as these caps are across the bridge outputs. This is important because they serve as snubbers and a lot of high frequency energy is dissipated in them. The best package suitable is SM0805 type.

11.4 R1, R5: Thick film Type 1/4W \pm 5% 200ppm

The resistor type can either Metal film or Thick film 1/4W, 5% tolerance. These act to damp transients to amplifier when outputs are unloaded and useful at high frequencies. The suitable package could be surface mount SM1210 type.

11.5 C27, C28: 100nF 50V X7R \pm 10%

These bypass the high frequency EMI for the Amp Power Supply.

The suitable type is MLC X7R with 50VDC rating and SM0805 package. These should be placed as near as possible to Power Chip to be effective.

11.6 C6, C20: 470nF, 63V, \pm 5% Polyester Film

These form the differential LC filter along with inductor L1, L2, L3 and L4 respectively. These must be Polyester Film Dielectric type with 63VDC voltage rating. The important specification to be looked for while selecting is dissipation factor (tan d versus frequency curve), which should be 0.01 @ 10KHz and must be non-inductive construction also.

Be careful in selecting normal film capacitor that are inductive. The case size is not critical, but Box Type will be preferable, as they remain flush to the PCB.

11.7 L1, L2, L3, L4: 22 μ H @ 3A Inductor

These are important component in output filter circuit. The important specifications to look for are DC resistance value, magnetic material and DC current capability. Also, the DC saturation current specification must be looked for. The saturated inductor can cause the filter performance to degrade. The typical specs are:

DC current capacity: 3A for 35W and 3.5A for 50W.

The types to look for should be power inductors for switching applications. Be careful in placement of these, if L1, L2 are very near to L3, L4 can give degradation on crosstalk figure due to magnetic coupling.

11.8 C4: 1000 μ F 50V \pm 20% Aluminum Electrolytic

This can be aluminum electrolytic capacitor with 35VDC rating with \pm 20% tolerance. The important specification to look for is (tan d) typically around 0.12 @ 120Hz. Please note the impedance of Electrolytic capacitor increases at higher frequencies so select LOW ESR if possible.

The package can be decided based upon individual requirement. Radial can types are suitable.

11.9 C1, C13, C16, C26: 100nF, 50V, X7R, \pm 10%

These filter capacitors on the output along with L1, L2, L3, L4 form an LC filter circuit to bypass common mode signals. These also must be MLC X7R types with 50VDC voltage rating. The recommended package is SM0805. The X7R is important here as this is the main filter component in bypassing the high frequency from the output.

11.10 C2, C11, C18, C25: 100nF, 50V, X7R, \pm 10%

These act as secondary Roll Off for R2, R3, R6 and R7 respectively. The recommended type is MLC X7R with 50VDC rating and SM0805 package.

11.11 C5: 100nF 25V

This capacitor is a bypass for 3.3V. Is not very critical but noise on the 3.3V supply can cause the degradation of internal clocks leading to poor signal to noise ratio and THD+N.

The type suitable could be X7R type MLC with \pm 20%, 25VDC.

11.12 R2, R3, R6, R7: Thick film type 1/4W, 5%

The resistors type can either metal film or thick film depending on the suitability but note these must be 1/4W rating & tolerance of 5%, as they form RC filter circuits. The suitable package could be Surface mount SM1210 type

11.13 R4, R8: Thick film type 1/10W 10%

Surface mount SM0805 could be suitable. This is not a critical component.

12 HEATSINK CHOICE

12.1 STA500

Thermal resistance junction to case (copper tab) $R_{th_j-c} = \sim 1^{\circ}C/W$
Intervention of the thermal junction $T_{j_max} = 150^{\circ}C$

The thermal resistance junction to ambient, for the on board heatsink, is dominated by the board layout and can vary from

- $R_{th_j-a} = 50^{\circ}C/W$ (no copper surface dedicated to power dissipation), to
- $R_{th_j-a} = 15^{\circ}C/W$ (6 cm² surface + groundplane + 16 via holes).

The threshold junction temperature for the warning signal switch on is $T_{j_tw} = 130^{\circ}C/W$ (no other effect on the functionality)

This power dissipation with very low signal (all bridges switching) is

- $P_{diss_idle} = \sim 1.5W @ V_{cc} = 28V$

12.2 STA50x

$V_{cc} = 40V$ correspond at $P_{out} = 80W$ per channel

$P_{out\ TOT} = 160W$

Efficiency = 90% (for maximum power)

$P_{lost} = 16W$

$T_j = 150^{\circ}C$ junction temperature)
 $T_{amb} = 50^{\circ}C$ (environment temperature)

$$R_{th} = \frac{T_j - T_{amb}}{P_{lost}} = \frac{150 - 50}{16} = 6.25^{\circ}C/W$$

For further information on the heatsink choice, please refer to AN1965.

Table 7. Revision History

Date	Revision	Description of Changes
June 2004	1	First Issue
May 2006	2	Modified figure 2.

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